

isc Silicon NPN Darlington Power Transistor

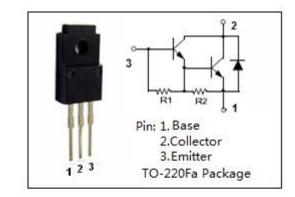
BDT61F

DESCRIPTION

- · High DC Current Gain
- · Low Saturation Voltage
- · Complement to Type BDT60F
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

 Designed for use as complementary AF push-pull output stage applications

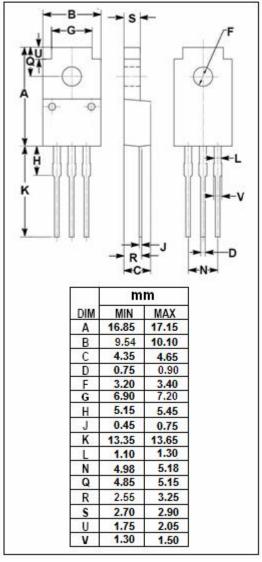


ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--|---------|--------------|--|
| V _{CBO} | Collector-Base Voltage | 60 | V | |
| V _{CEO} | Collector-Emitter Voltage | 60 | V | |
| V _{EBO} | Emitter-Base Voltage | 5 | V | |
| Ic | Collector Current-Continuous | 4 | Α | |
| I _{CP} | Collector Current-Peak | 6 | Α | |
| I _B | Base Current-Continuous | 0.1 | Α | |
| Pc | Collector Power Dissipation @ T _a =25°C | 17 | W | |
| | Collector Power Dissipation @ Tc=25℃ | 25 | | |
| TJ | Junction Temperature 150 | | $^{\circ}$ C | |
| T _{stg} | Storage Temperature Range | -65~150 | $^{\circ}$ | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT | |
|---------------------|--|-----|------|--|
| R _{th j-c} | Thermal Resistance, Junction to Case | 5 | °C/W | |
| R _{th j-a} | R _{th j-a} Thermal Resistance,Junction to Ambient | | °C/W | |





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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | МАХ | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-Emitter Breakdown Voltage | I _C = 30mA; I _B = 0 | 80 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 1.5A; I _B = 6mA | | | 2.5 | V |
| V _{BE(on)} | Base-Emitter On Voltage | Ic= 4A; Vc= 3V | | | 2.5 | V |
| І _{сво} | Collector Cutoff Current | V _{CB} = 30V; I _E = 0 | | | 0.2 | - mA |
| | | V _{CB} = 40V; I _E = 0; T _C = 150°C | | | 1.0 | |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 40V; I _B = 0 | | | 0.2 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 5 | mA |
| h _{FE-1} | DC Current Gain | I _C = 0.5A ; V _{CE} = 3V | | 2000 | | |
| h _{FE-2} | DC Current Gain | I _C = 1.5A ; V _{CE} = 3V | 750 | | | |
| h _{FE-3} | DC Current Gain | I _C = 4A; V _{CE} = 3V | | 1000 | | |

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